2N5588 (#23391)

RFQ/Sample

NPN Transistor

Division	Lawrence	**Datasheet**	(none)
Mil-Spec	(none)		
Shipping	(none)	**Qual Data**	Contact Microsemi

Package
TO-114(STD)

Maximum Electrical Rating	Symbol	Max	Unit
Power Dissipation	**Power**	350	W
Collector Current	**I_C**	80	A
Breakdown Voltage Collector -to-Base	**$B_{V(CBO)}$**	160	V
Voltage Collector to Emitter Open	**V_{CEO}**	160	V
Voltage Emitter to Base Open	**BV_{EBO}**	6	V

Electrical Rating	Symbol	Min	Typ	Max	Unit
Collector Emitter Saturation Voltage					
(I_B=0.8 mA, I_C=80 mA, T_A=25 ºC,300µ s pulse)	**$V_{CE(sat)}$**			2	V
DC Current Gain					
(I_C=80 mA, T_A=25 ºC,300µ s pulse)	**HFE**	10		30